



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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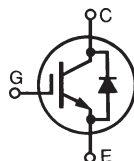
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



High-Gain IGBT w/ Diode

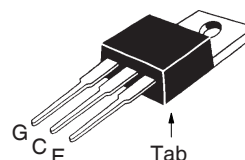
IXGP24N60C4D1

High-Speed PT Trench IGBT



$$\begin{aligned} V_{CES} &= 600V \\ I_{C110} &= 24A \\ V_{CE(sat)} &\leq 2.70V \\ t_{fi(typ)} &= 44ns \end{aligned}$$

TO-220



G = Gate C = Collector
E = Emitter Tab = Collector

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	600	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}, R_{GE} = 1M\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	56	A
I_{C110}	$T_C = 110^\circ\text{C}$	24	A
I_{F110}	$T_C = 110^\circ\text{C}$	30	A
I_{CM}	$T_C = 25^\circ\text{C}, 1\text{ms}$	130	A
SSOA (RBSOA)	$V_{GE} = 15V, T_{VJ} = 125^\circ\text{C}, R_G = 10\Omega$ Clamped Inductive Load	$I_{CM} = 48$ @ $\leq V_{CES}$	A
P_C	$T_C = 25^\circ\text{C}$	190	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ\text{C}$
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	$^\circ\text{C}$
M_d	Mounting Torque	1.13/10	Nm/lb.in.
Weight		3	g

Features

- Optimized for Low Switching Losses
- Square RBSOA
- Anti-Parallel Ultra Fast Diode
- International Standard Package

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_{GE(th)}$	$I_C = 250\mu\text{A}, V_{CE} = V_{GE}$	4.0		6.5 V
I_{CES}	$V_{CE} = V_{CES}, V_{GE} = 0V$ $T_J = 125^\circ\text{C}$			10 μA 1.5 mA
I_{GES}	$V_{CE} = 0V, V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = I_{C110}, V_{GE} = 15V, \text{Note 1}$ $T_J = 125^\circ\text{C}$		2.10 1.95	2.70 V V

Symbol Test Conditions

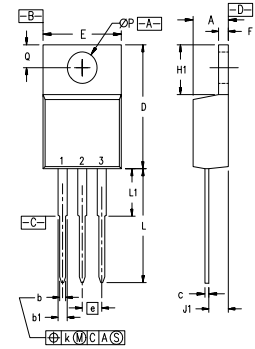
($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

Characteristic Values

Min. Typ. Max.

g_{fs}	$I_C = I_{C110}, V_{CE} = 10V, \text{Note 1}$	10	17	S
C_{ies}	$V_{CE} = 25V, V_{GE} = 0V, f = 1\text{MHz}$		875	pF
C_{oes}			62	pF
C_{res}			28	pF
Q_g	$I_C = I_{C110}, V_{GE} = 15V, V_{CE} = 0.5 \cdot V_{CES}$		64	nC
Q_{ge}			7	nC
Q_{gc}			28	nC
$t_{d(on)}$	Inductive Load, $T_J = 25^\circ\text{C}$ $I_C = I_{C110}, V_{GE} = 15V$ $V_{CE} = 360V, R_G = 10\Omega$ Note 2		22	ns
t_{ri}			43	ns
E_{on}			0.35	mJ
$t_{d(off)}$			192	ns
t_{fi}			44	ns
E_{off}			0.34	mJ
$t_{d(on)}$	Inductive Load, $T_J = 125^\circ\text{C}$ $I_C = I_{C110}, V_{GE} = 15V$ $V_{CE} = 360V, R_G = 10\Omega$ Note 2		20	ns
t_{ri}			32	ns
E_{on}			0.37	mJ
$t_{d(off)}$			148	ns
t_{fi}			115	ns
E_{off}			0.52	mJ
R_{thJC}			0.65	$^\circ\text{C/W}$
R_{thCS}				$^\circ\text{C/W}$

TO-220 (IXGP) Outline



Pins: 1 - Gate 2 - Collector
3 - Emitter

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

Reverse Diode (FRED)

Symbol Test Conditions

($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)

Characteristic Values

Min. Typ. Max.

V_F	$I_F = 10A, V_{GE} = 0V, \text{Note 1}$		3.0	V
I_{RM}	$I_F = 12A, V_{GE} = 0V,$ $-di_F/dt = 100A/\mu s, V_R = 100V, T_J = 125^\circ\text{C}$		2.5	A
t_{rr}			110	ns
t_{rr}	$I_F = 1A, V_{GE} = 0V, -di_F/dt = 100A/\mu s, V_R = 30V$		30	ns
R_{thJC}			2.5	$^\circ\text{C/W}$

Notes:

1. Pulse test, $t \leq 300\mu s$, duty cycle, $d \leq 2\%$.
2. Switching times & energy losses may increase for higher $V_{CE}(\text{clamp})$, T_J or R_G .

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	